

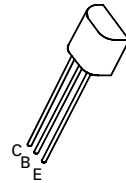
PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

2N6726 2N6727

ISSUE 1 – MARCH 94

FEATURES

- * 40 Volt V_{CEO}
- * Gain of 50 at $I_C = 1$ Amp
- * $P_{tot} = 1$ Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	2N6726	2N6727	UNIT
Collector-Base Voltage	V_{CBO}	-40	-50	V
Collector-Emitter Voltage	V_{CEO}	-30	-40	V
Emitter-Base Voltage	V_{EBO}	-5		V
Peak Pulse Current	I_{CM}	-2		A
Continuous Collector Current	I_C	-1		A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	1		W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	2N6726		2N6727		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		-50		V	$I_C = -1\text{mA}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		-40		V	$I_C = -10\text{mA}, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -1\text{mA}, I_C = 0$
Collector Cut-Off Current	I_{CBO}		-0.1		-0.1	μA	$V_{CB} = -40\text{V}, I_E = 0$ $V_{CB} = -50\text{V}, I_E = 0$
Emitter Cut-Off Current	I_{EBO}		-0.1		-0.1	μA	$V_{EB} = -5\text{V}, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5		-0.5	V	$I_C = -1\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2		-1.2	V	$I_C = -1\text{A}, V_{CE} = -1\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	55 60 50	250	55 60 50	250		$I_C = -10\text{mA}, V_{CE} = -1\text{V}^*$ $I_C = -100\text{mA}, V_{CE} = -1\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -1\text{V}^*$
Transition Frequency	f_T	50	500	50	500	MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$
Collector Base Capacitance	C_{CB}		30		30	pF	$V_{CE} = -10\text{V}, f = 1\text{MHz}$